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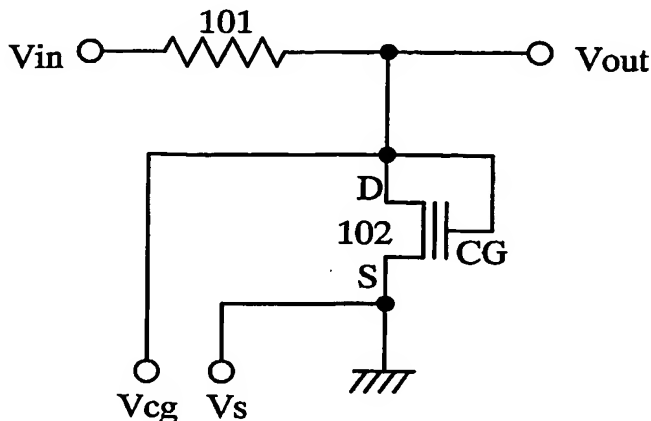
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(54) Title: LIMITER AND SEMICONDUCTOR DEVICE USING THE SAME



(57) Abstract: The limiter of the invention uses
as a diode a stacked gate thin film transistor (TFT)
including a floating gate. When the TFT includ-
ing a floating gate is used, the threshold voltage
V_{th} may be corrected by controlling the amount
of charge accumulated in the floating gate even in
the case where there are variations in the thresh-
old voltages V_{th} of the TFT.